TOSHIBA Photocoupler GaAs Ired & Photo-Triac

TLP560J

Triac Driver
Programmable Controllers
AC-Output Module
Solid State Relay

勝特力電材超市-龍山店 886-3-5773766 勝特力電材超市-光復店 886-3-5729570 胜特力电子(上海) 86-21-34970699 胜特力电子(深圳) 86-755-83298787 http://www.100y.com.tw

The TOSHIBA TLP560J consists of a photo-triac optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

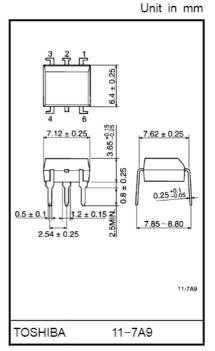
- Peak off-state voltage: 600V(min.)
- On-state current: 100mA(max.)
- Isolation voltage: 2500Vrms (min.)
- UL recognized: UL1577, file no. E67349
- Trigger LED current

Classi- fication*	Trigger LED Current (mA) V _T =6V, Ta=25°C		Marking Of Classification
lication	Min.	Max.	Classification
(IFT7)	_	7	Т7
Standard	_	10	T7, blank

*Ex. (IFT7); TLP560J(IFT7)

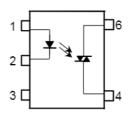
(Note) Application type name for certification test, please use standard product type name, i.e. TLP560J(IFT7): TLP560J

*1: According to VDE0110, table 4.



Weight: 0.39 g

Pin Configuration (top view)



- 1: Anode
- 2: Cathode
- 3: N.C.
- 4: Terminal 1
- 6: Terminal 2

Maximum Ratings (Ta = 25°C)

Characteristic			Symbol	Rating	Unit	
	Forward current	IF	50	mA		
İ	Forward current derating (Ta ≥ 53	ΔI _F / °C	-0.7	mA / °C		
LED	Peak forward current (100µs pulse	e, 100pps)	I _{FP}	1	Α	
	Reverse voltage	VR	5	V		
	Junction temperature	Tj	125	°C		
	Off-state output terminal voltage	V _{DRM}	600	V		
	On–state RMS current	Ta=25°C	l=m.uo.	100	mA	
L	On-State Rivis current	Ta=70°C	I _{T(RMS)}	50	l IIIA	
Detector	On–state current derating(Ta ≥ 25	ΔI _T / °C	-1.1	mA / °C		
Det	Peak on-state current (100µs puls	I _{TP}	2	А		
	Peak nonrepetitive surge current (Pw=10ms,DC=10%)	I _{TSM}	1.2	А		
	Junction temperature	Tj	115	°C		
Storage temperature range			T _{stg}	-55~125	°C	
Operating temperature range			T _{opr}	-40~100	°C	
Lead soldering temperature (10s)			T _{sol}	260	°C	
Isola	tion voltage (AC, 1min., R.H. ≤ 60%	BVS	3V _S 2500			

Recommended Operating Conditions

Characteristic	Symbol	Min. Typ.		Max.	Unit
Supply voltage	VAC	_	_	240	Vac
Forward current	lF	15	20	25	mA
Peak on-state current	ITP	_	_	_	А
Operating temperature	T _{opr}	-25	_	85	°C

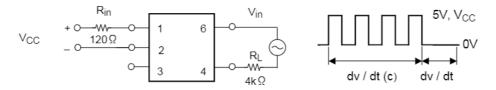
Individual Electrical Characteristics (Ta = 25°C)

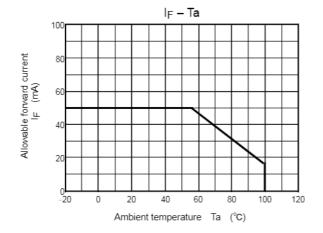
	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Г	Forward voltage	VF	I _F =10mA	1.0	1.15	1.3	V
	Reverse current	IR	V _R =5V	_	_	10	μΑ
	Capacitance	CT	V=0, f=1MHz	_	10	_	pF
	Peak off-state current	IDRM	V _{DRM} =600V	_	10	1000	nA
	Peak on-state voltage	V _{TM}	I _{TM} =100mA	_	1.7	3.0	V
go	Holding current	I _H	_	_	1.0	_	mA
Detector	Critical rate of rise of off–state voltage	dv / dt	V _{in} =240V _{rms,} Ta=85°C (fig.1)	_	500	_	V / µs
	Critical rate of rise of commutating voltage	dv / dt(c)	V _{in} =60 V _{rms} , I _T =15mA (fig.1)	_	0.2	_	V/µs

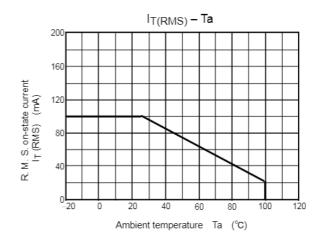
Coupled Electrical Characteristics (Ta = 25°C)

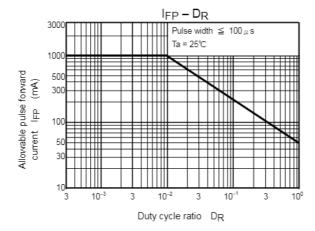
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Trigger LED current	I _{FT}	V_T =6 V , R_L =100 Ω	_	5	10	mA
Capacitance (input to output)	CS	V _S =0, f=1MHz	_	0.8	_	pF
Isolation resistance	R _S	V _S =500V	5×10 ¹⁰	10 ¹⁴	_	Ω
	BVS	AC, 1 minute	2500	_	_	V _{rms}
Isolation voltage		AC, 1 second, in oil	_	5000	_	
		DC, 1 minute, in oil	_	5000	_	V _{dc}

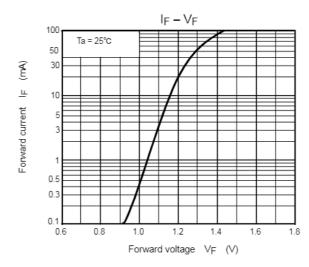
Fig.1: dv / dt test circuit

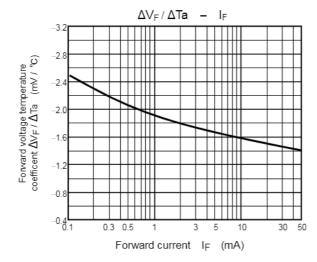


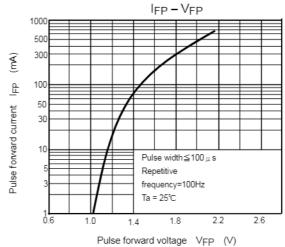


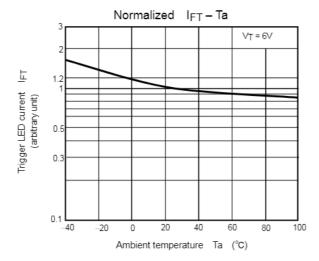


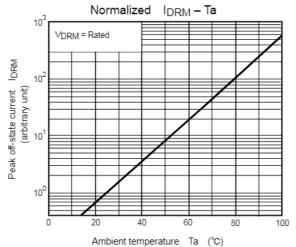


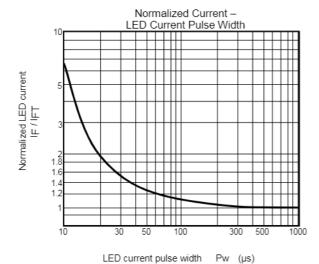


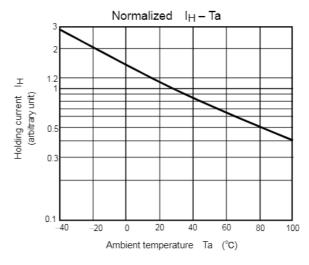


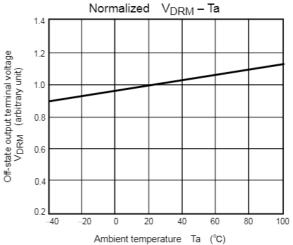












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